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SPRINGFIELD, NEW JERSEY 07081
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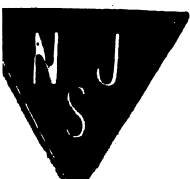
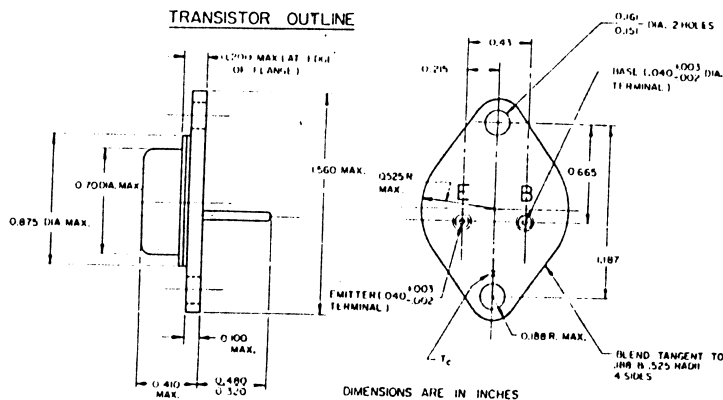
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N-P-N SILICON TRANSISTOR

$\frac{V_{CEX}}{V}$	$\frac{V_{CER}}{V}$	$\frac{V_{CEO}}{V}$	$\frac{V_{EBO}}{V}$	$\frac{I_C}{A}$	$\frac{I_B}{A}$	$\frac{P_c}{W}$	$\frac{T_{storage}}{^{\circ}C}$	$\frac{T_J}{^{\circ}C}$
90	65	55	7	15	7	117	-65 to +200	-65 to +200

<u>Characteristic</u>	<u>Symbol</u>	<u>Min.</u>	<u>Max.</u>	<u>Unit</u>
DC Current Gain*				
IC = 4 A, VCE = 4 V	hFE	20	70	—
Collector-to-Emitter Voltage*				
IC = 100 mA	VCEO	55	—	V
Collector-to-Emitter Saturation Voltage*				
IC = 4 A, IB = 400 mA	VCE(s)	—	1.1	V
Base-to-Emitter Saturation Voltage*				
IC = 4 A, IB = 400 mA	VBE(s)	—	1.8	V
Collector Cutoff Current				
VCEX = 90 V, VBE = -1.5 V	ICEX	—	5	mA
VCER = 65 V, RBE = 100 ohms	ICER	—	5	mA
Emitter Cutoff Current				
VEBO = 7 V	IEBO	—	5	mA
Thermal Resistance				
Junction-to-Case	θ_{J-C}	—	1.5	°C/W

*Pulse width $\leq 300 \mu\text{sec}$, duty cycle $\leq 2\%$.



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